--15. The silicon single crystal wafer according to Claim 13, wherein the interstitial oxygen concentration is 5 ppma or less.--

--16. The silicon single crystal wafer according to Claim 14, wherein the interstitial oxygen concentration is 5 ppma or less.--

--17. The silicon single crystal wafer according to Claim 13, wherein the concentration of the doped nitrogen is 1×10^{14} number/cm^3 or more.--

--18. The silicon single crystal wafer according to Claim 14, wherein the concentration of the doped nitrogen is 1×10^{14} number/cm^3 or more.--

--19. The silicon single crystal wafer according to Claim 13, wherein the concentration of the doped nitrogen is 5×10^{14} number/cm^3 or more.--

--20. The silicon single crystal wafer according to Claim 14, wherein the concentration of the doped nitrogen is 5×10^{14} number/cm^3 or more.--

--21. The silicon single crystal wafer according to Claim 13, wherein one main surface of the silicon single crystal wafer is subjected to an EG treatment.--

--22. The silicon single crystal wafer according to Claim 14, wherein one main surface of the silicon single crystal wafer is subjected to an EG treatment.--

--23. An SOI wafer, wherein a silicon single crystal wafer according to Claim 13 is used as an SOI layer.--

--24. An SOI wafer, wherein a silicon single crystal wafer according to Claim 14 is used as an SOI layer.--

--25. A method for producing a silicon single crystal wafer, wherein the wafer is produced from a single crystal pulled under such conditions that the crystal should have an N-region for the entire plane and interstitial oxygen concentration should become 8 ppma or less when the crystal is grown by the Czochralski method with nitrogen doping.--

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--26. The method for producing a silicon single crystal wafer according to Claim 25, wherein the wafer is produced from a single crystal grown with a concentration of doped nitrogen of 1 x 10^{14} number/cm^3 or more and an F/G value (F: pulling rate, G: crystal solid-liquid interface temperature gradient) in a range of 0.14-0.22 mm^2/K•min at any point of crystal plane as such a condition that the entire plane of the crystal should become an N-region.--

--27. The method for producing a silicon single crystal wafer according to Claim 25, wherein the wafer is produced from a single crystal grown with a concentration of doped nitrogen of 5 x 10^{14} number/cm^3 or more and an F/G value in a range of 0.12-0.24 mm^2/K•min at any point of crystal plane as such a condition that the entire plane of the crystal should become an N-region.--

--28. A method for producing a silicon single crystal wafer, wherein a silicon single crystal wafer produced by a production method according to Claim 25 is subjected to a heat treatment--.

--29. A method for producing a silicon single crystal wafer, wherein a silicon single crystal wafer produced by a production method according to Claim 26 is subjected to a heat treatment.--

--30. A method for producing a silicon single crystal wafer, wherein a silicon single crystal wafer produced by a production method according to Claims 27 is subjected to a heat treatment.--

--31. The method for producing a silicon single crystal wafer according to Claim 28, wherein the heat treatment is performed by using a rapid thermal annealer.--

--32. The method for producing a silicon single crystal wafer according to Claim 29, wherein the heat treatment is performed by using a rapid thermal annealer.--